

# NPN SILICON PLANAR TRANSISTOR

#### **FEATURES**

\* Power dissipation

Pc:0.25 W (Tamb=25°C)

\* Collector current Ic: 0.1

\* Collector-base voltage

V<sub>CBO</sub>: 30

\* Operating and storage junction temperature range

T<sub>J</sub>,Tstg: -55°C to +150°C

# **MECHANICAL DATA**

\* Case: Molded plastic

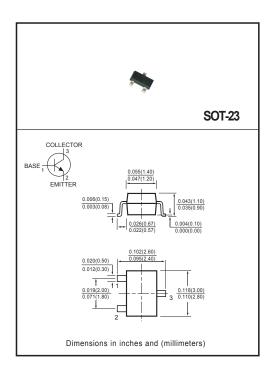
\* Epoxy: UL 94V-O rate flame retardant

\* Lead: MIL-STD-202E method 208C guaranteed

\* Mounting position: Any \* Weight: 0.008 gram

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase , half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.



#### ABSOLUTE MAXIMUM RATINGS

DESCRIPTION	SYMBOL	VALUE	UNITS
Collector-base Voltage	V <sub>CBO</sub>	30	V
Collector-emitter Voltage	V <sub>CEO</sub>	30	V
Emitter-base Voltage	V <sub>EBO</sub>	5.0	٧
Collector Current	Ic	100	mA
Collector Dissipation	Pc	250	
Operation And Storage Junction	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### **ELECTRICAL CHARACTERISTICS** ( @ TA = 25<sup>0</sup>C unless otherwise noted )

CHARACTERISTICS	SYMBOL	MIN	TYP	MAX	UNITS
Collector-base Voltage (I <sub>C</sub> = 100μA, I <sub>E</sub> =0)	V <sub>CBO</sub>	30	-	-	V
Collector-emitter Voltage (I <sub>C</sub> = 1mA, I <sub>B</sub> =0)	V <sub>CEO</sub>	30	-	-	V
Emitter-base Voltage (I <sub>E</sub> = 100μA, I <sub>C</sub> =0)	V <sub>EBO</sub>	5.0	-	-	V
Collector Cut-off Current (V <sub>CB</sub> = 30V, I <sub>E</sub> =0)	I <sub>CBO</sub>	-	-	15	nA
Emitter Cut-off Current (V <sub>EB</sub> = 5V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	-	500	nA
DC Current Gain (I <sub>C</sub> = 1mA, V <sub>CE</sub> = 5V)	hFE	150	-	1000	-
Collector-emitter Saturation Voltage (I <sub>C</sub> = 100mA, I <sub>B</sub> = 5mA)	V <sub>CE(sat)</sub>	-	-	0.60	V
Base-emitter Voltage ((I <sub>C</sub> = 100mA, I <sub>B</sub> = 5mA)	V <sub>BE(sat)</sub>	-	-	1.2	V
Transition Frequency (V <sub>CE</sub> = 5V, I <sub>C</sub> = -10mA, f=100MHz)	f⊤	125	-	-	MHz
Output Capacitance ((V <sub>CB</sub> = 10V, f= 1MHz)	C <sub>ob</sub>	-	-	3.5	pF
Noise Figure (V <sub>CE</sub> = 5V, I <sub>C</sub> = 200uA, f=1KHz)	NF	-	-	4.0	dB

CLASSIFICATION	CMBT9014	В	С	D
h <sub>FE</sub>	150-1000	100-300	200-600	400-1000
Marking	14	14B	14C	14D

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